



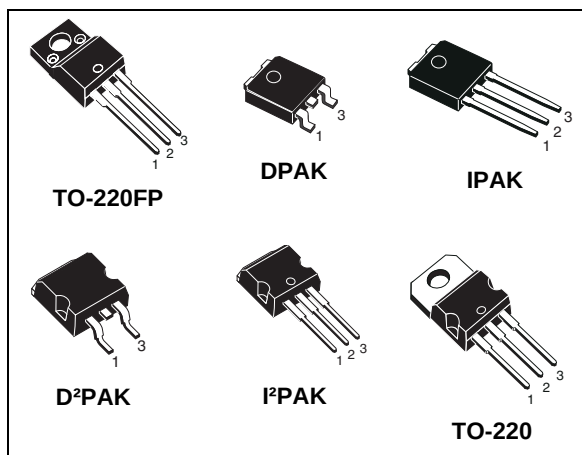
STB60N55F3, STD60N55F3, STF60N55F3 STI60N55F3, STP60N55F3, STU60N55F3

N-channel 55 V, 6.5 mΩ, 80 A, DPAK, IPAK, D²PAK, I²PAK, TO-220
TO-220FP STripFET™ III Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STB60N55F3	55V	<8.5mΩ	80A	110W
STD60N55F3	55V	<8.5mΩ	80A	110W
STF60N55F3	55V	<8.5mΩ	42A	30W
STI60N55F3	55V	<8.5mΩ	80A	110W
STP60N55F3	55V	<8.5mΩ	80A	110W
STU60N55F3	55V	<8.5mΩ	80A	110W

- Standard threshold drive
- 100% avalanche tested



Application

- Switching applications

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performances.

Figure 1. Internal schematic diagram

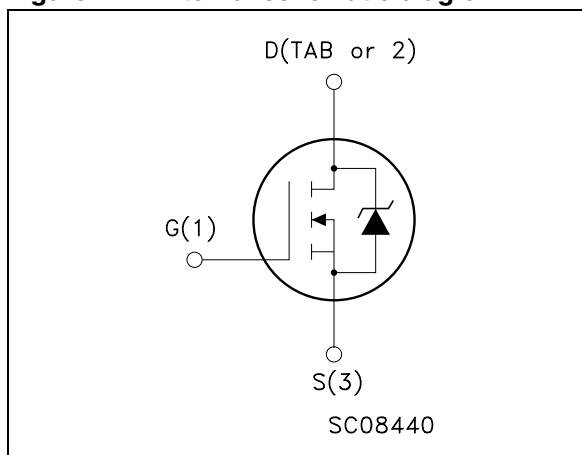


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB60N55F3	60N55F3	D ² PAK	Tape and reel
STD60N55F3	60N55F3	DPAK	Tape and reel
STF60N55F3	60N55F3	TO-220FP	Tube
STI60N55F3	60N55F3	I ² PAK	Tube
STP60N55F3	60N55F3	TO-220	Tube
STU60N55F3	60N55F3	IPAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK/D ² PAK TO-220 IPAK/I ² PAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS}=0$)	55		V
V_{GS}	Gate-source voltage	± 20		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	42	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	56	30	A
$I_{DM}^{(1)}$	Drain current (pulsed)	320	168	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	110	30	W
	Derating factor	0.73	0.2	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	11		V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	390		mJ
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{s}; T_C=25^\circ\text{C}$)		2500	V
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175		$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 80\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$. $T_j \leq T_{jmax}$
3. Starting $T_j=25^\circ\text{C}$, $I_D=32\text{ A}$, $V_{DD}=25\text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value					Unit
		DPAK	IPAK I ² PAK	D ² PAK	TO-220	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.36				5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50		35			$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max		100		62.5		$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose		275		300		$^\circ\text{C}$

1. When mounted on FR-4 board of 1inch², 2oz Cu

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A$, $V_{GS} = 0$	55			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$, $T_c = 125\text{ °C}$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V$, $I_D = 32A$		6.5	8.5	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 25V$, $I_D = 32A$	-	50		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V$, $f = 1MHz$, $V_{GS} = 0$	-	2200 500 25		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 27V$, $I_D = 65A$ $V_{GS} = 10V$ (see Figure 16)	-	33.5 12.5 9.5	45	nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 27V$, $I_D = 32A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 18)	-	20 50	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 27V$, $I_D = 32A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 18)	-	35 11.5	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Packages	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		DPAK-D ² PAK- I ² PAK-I ² PAK- TO-220	-		80 320	A A
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		TO-220FP	-		42 168	A A
V_{SD}	Forward on voltage	$I_{SD} = 65A$, $V_{GS} = 0$		-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 65A$, $V_{DD} = 30V$ $di/dt = 100A/\mu s$, $T_j = 150^{\circ}C$ (see Figure 17)		-	47 87 3.7		ns nC A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220
D²PAK / IPAK / I²PAK / DPAK

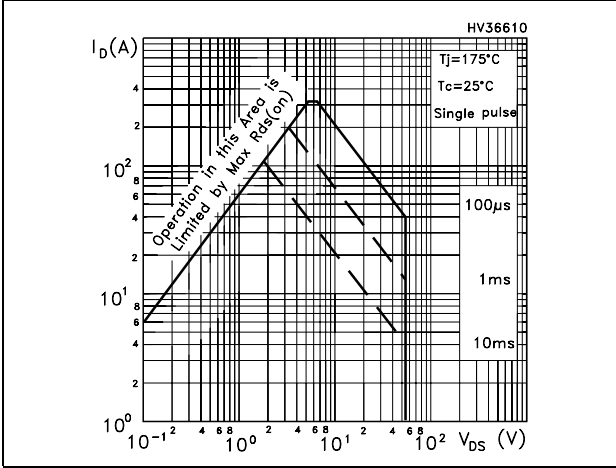


Figure 3. Thermal impedance for TO-220
D²PAK / IPAK / I²PAK / DPAK

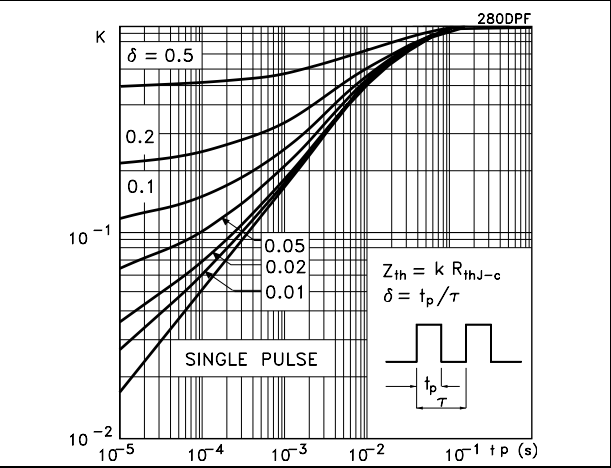


Figure 4. Safe operating area for TO-220FP

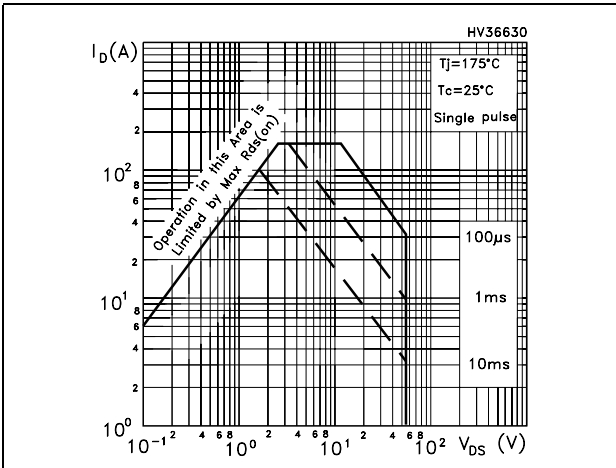


Figure 5. Thermal impedance for TO-220FP

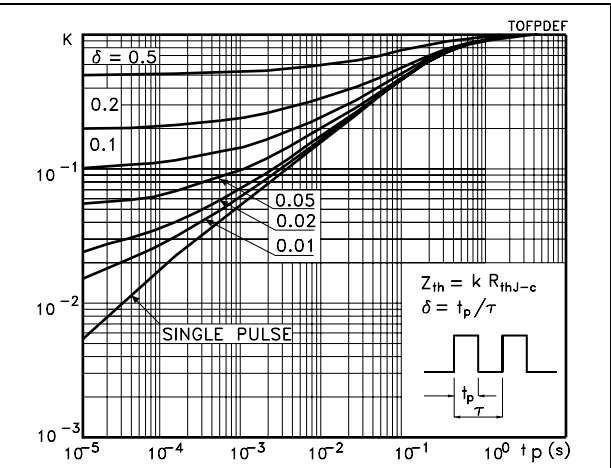


Figure 6. Output characteristics

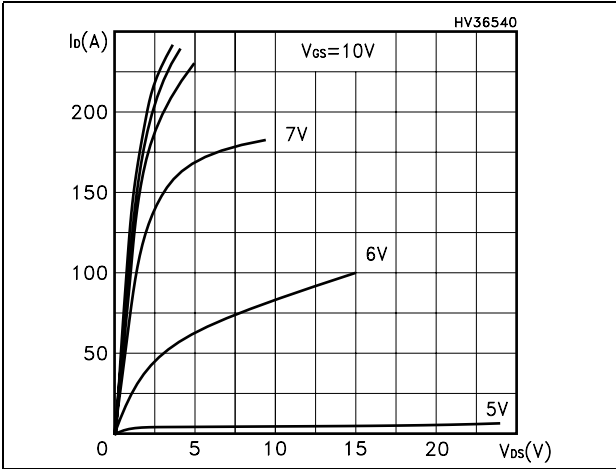


Figure 7. Transfer characteristics

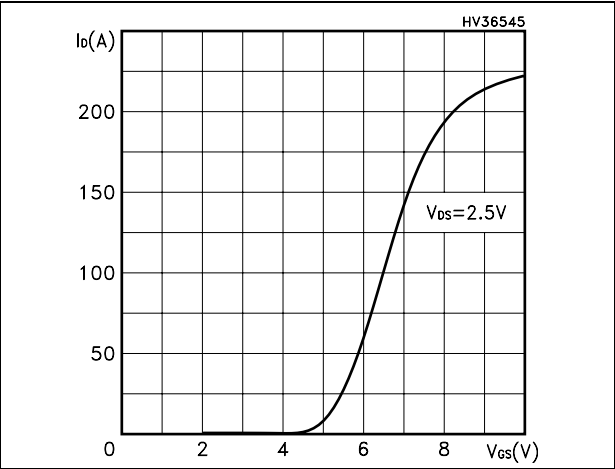


Figure 8. Normalized BV_{DSS} vs temperature

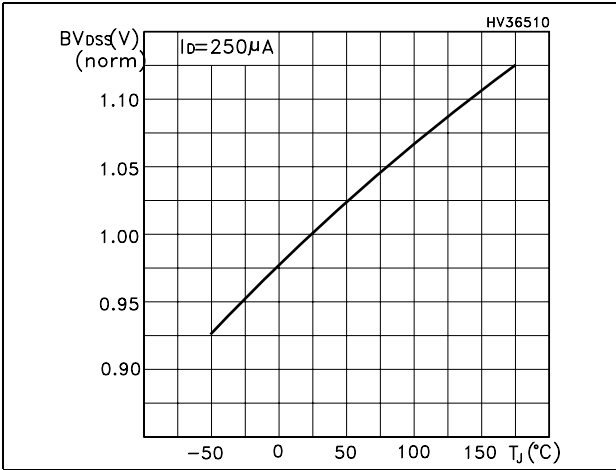


Figure 9. Static drain-source on resistance

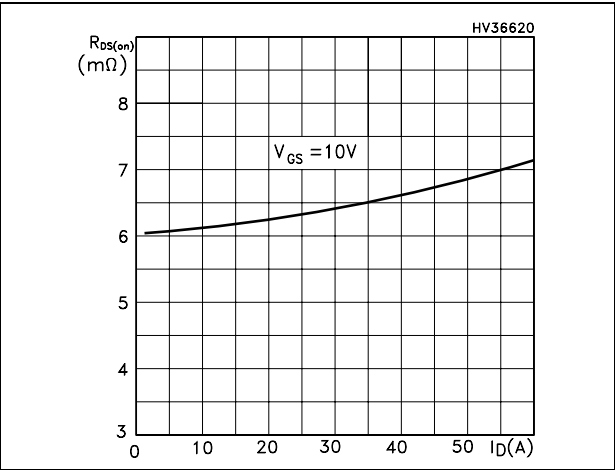


Figure 10. Gate charge vs gate-source voltage

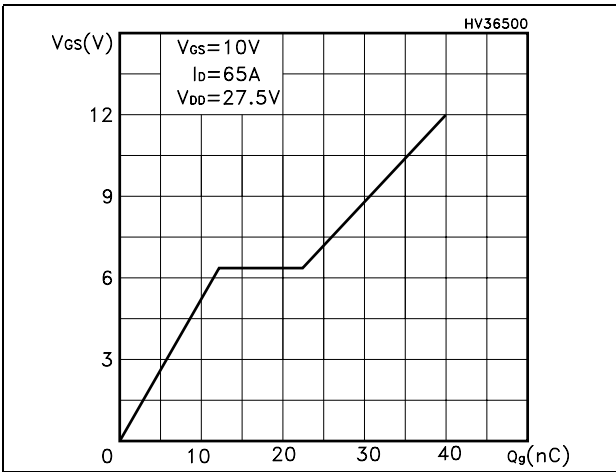


Figure 11. Capacitance variations

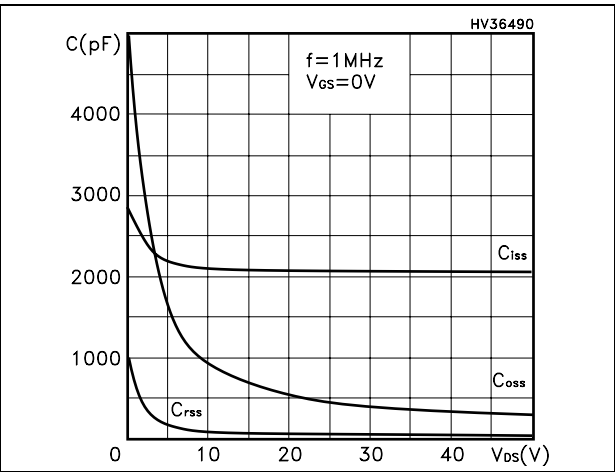


Figure 12. Normalized gate threshold voltage vs temperature

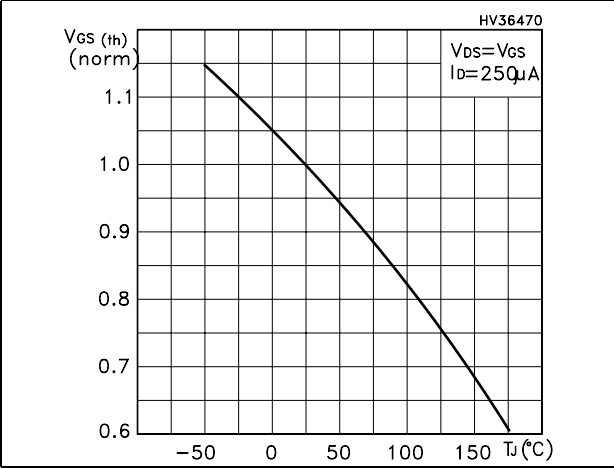


Figure 13. Normalized on resistance vs temperature

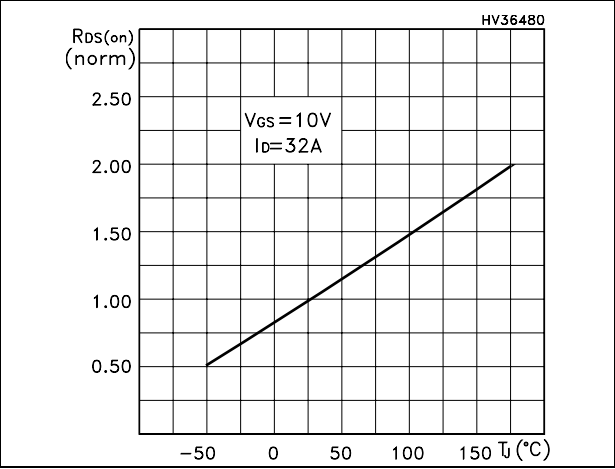
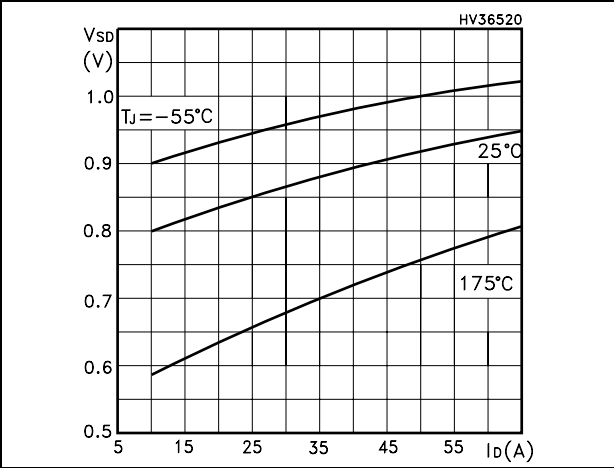


Figure 14. Source-drain diode forward characteristics



3 Test circuits

Figure 15. Switching times test circuit for resistive load

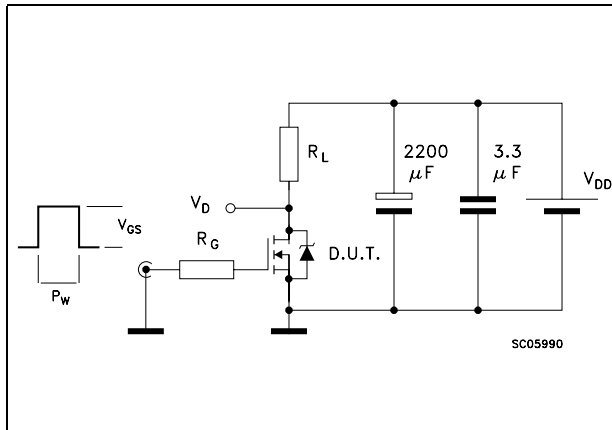


Figure 16. Gate charge test circuit

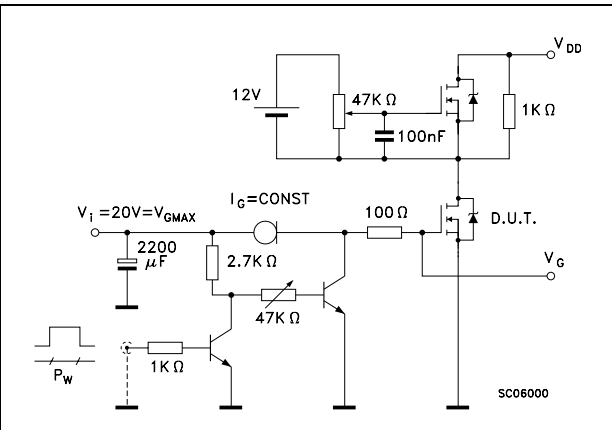


Figure 17. Test circuit for inductive load switching and diode recovery times

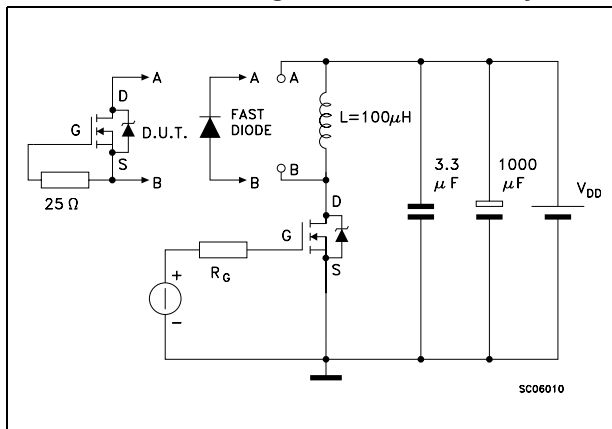


Figure 18. Unclamped inductive load test circuit

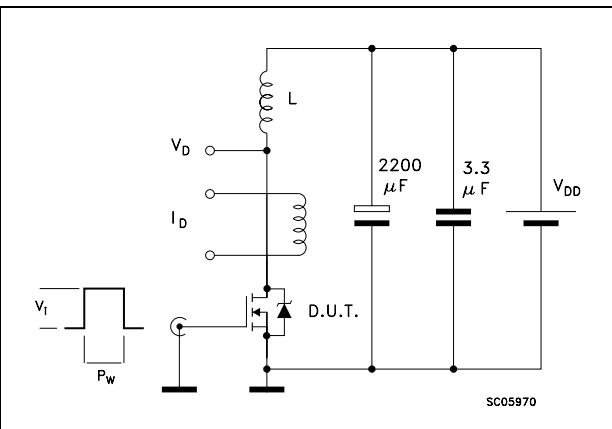


Figure 19. Unclamped inductive waveform

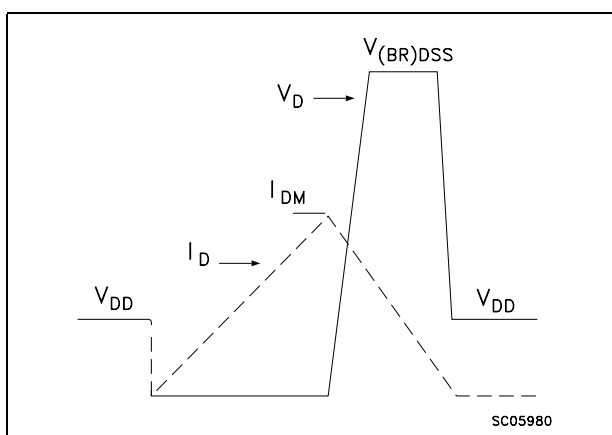
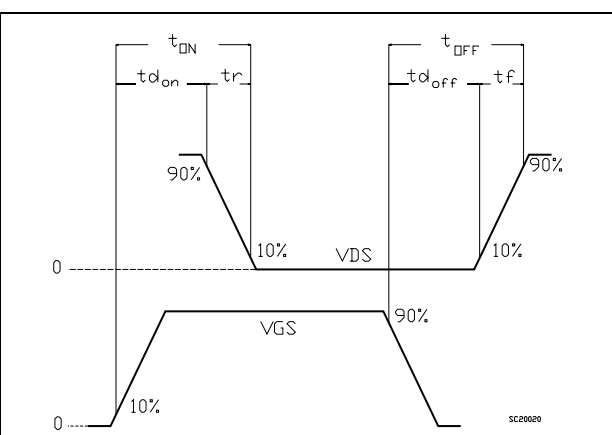


Figure 20. Switching time waveform

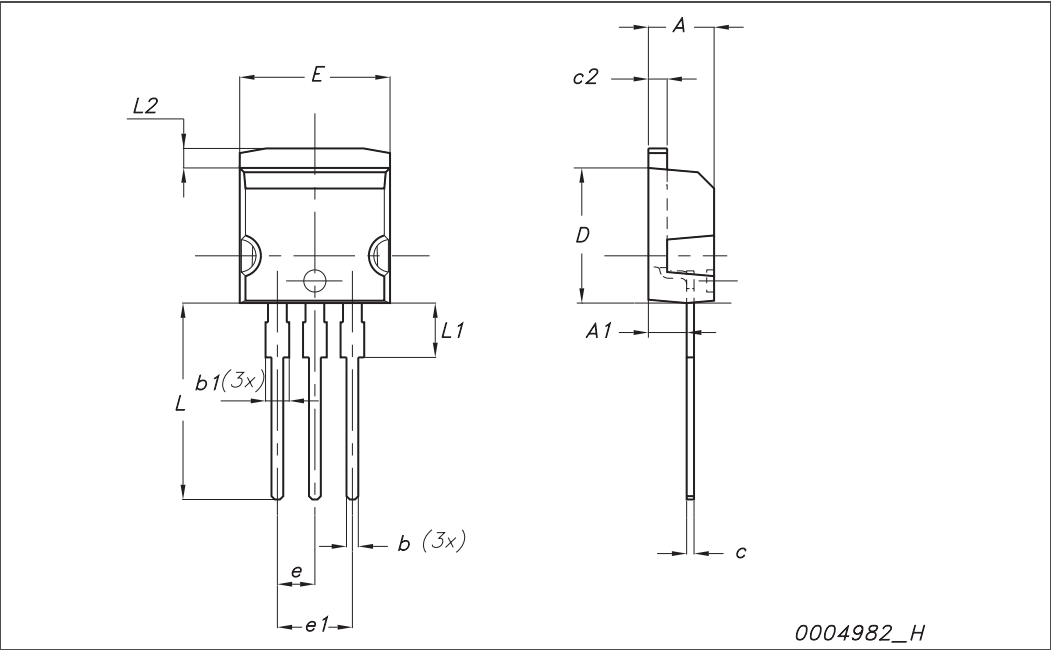


4 **Package mechanical data**

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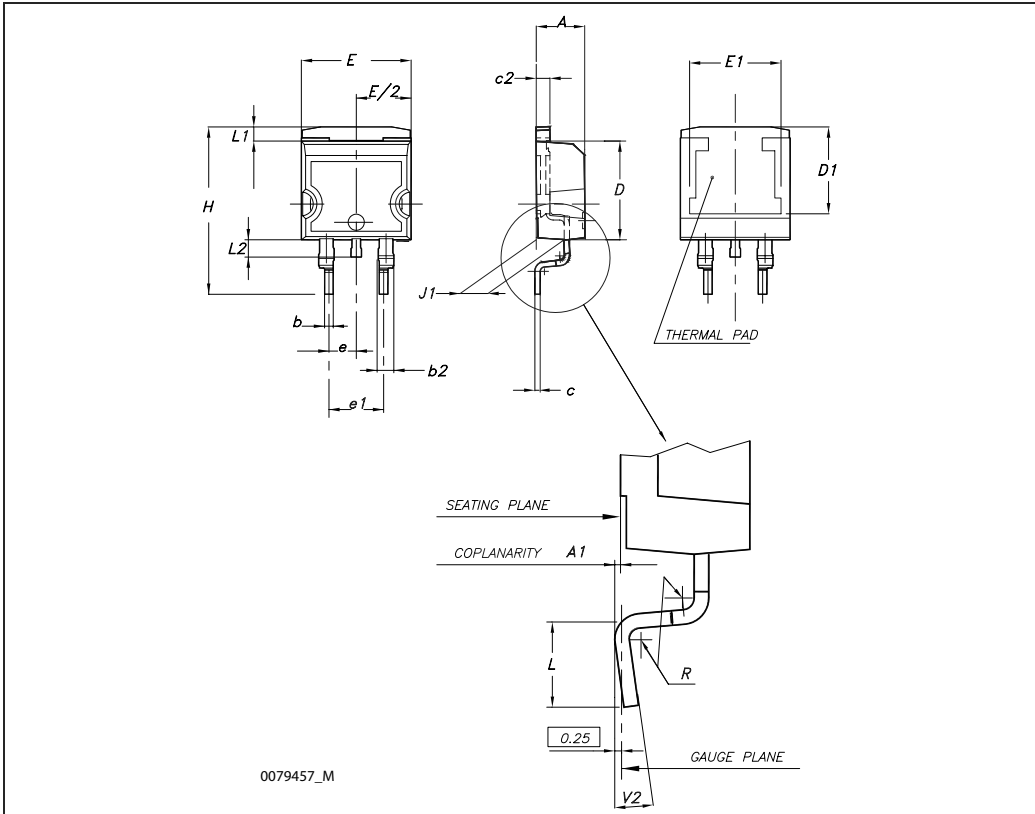
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



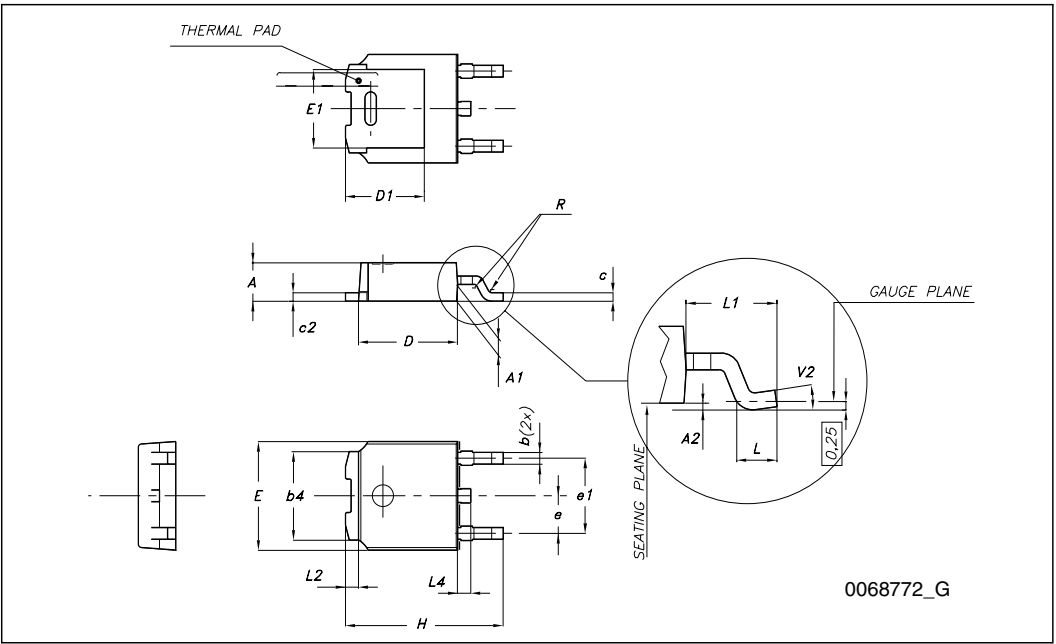
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



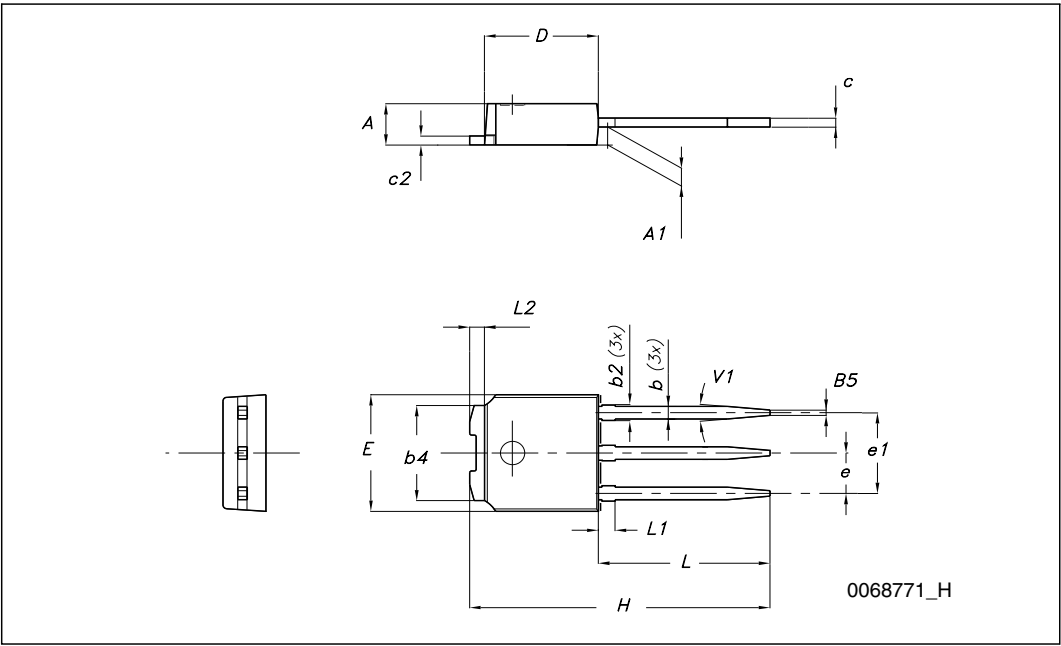
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



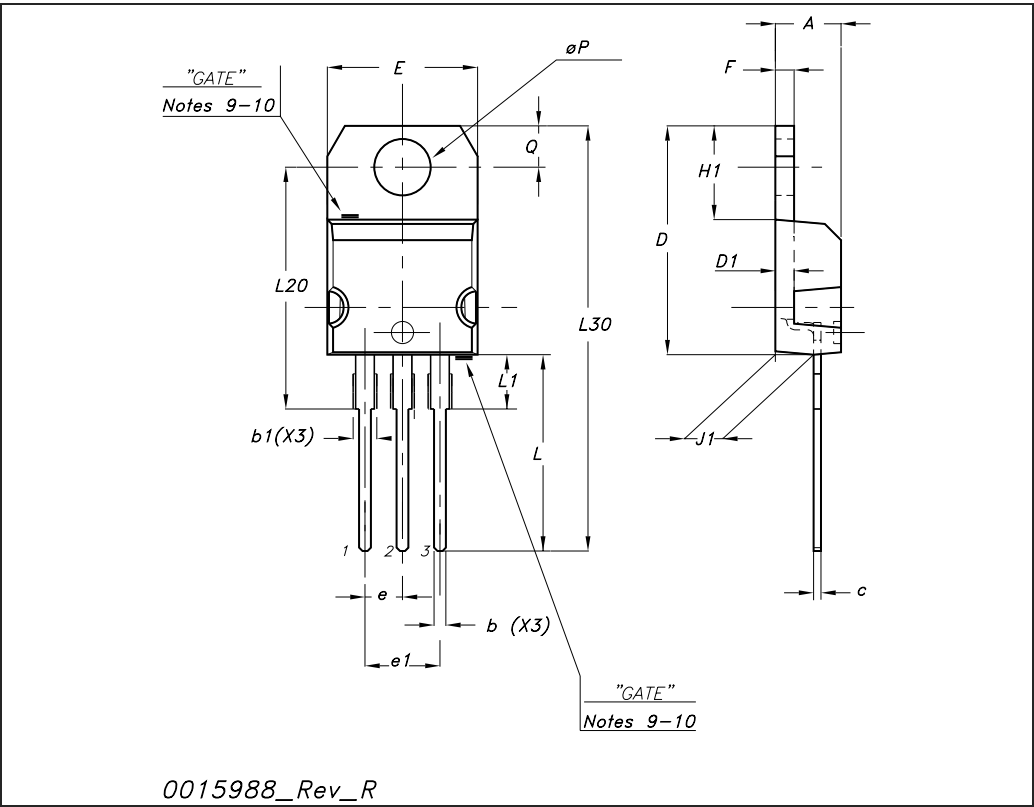
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



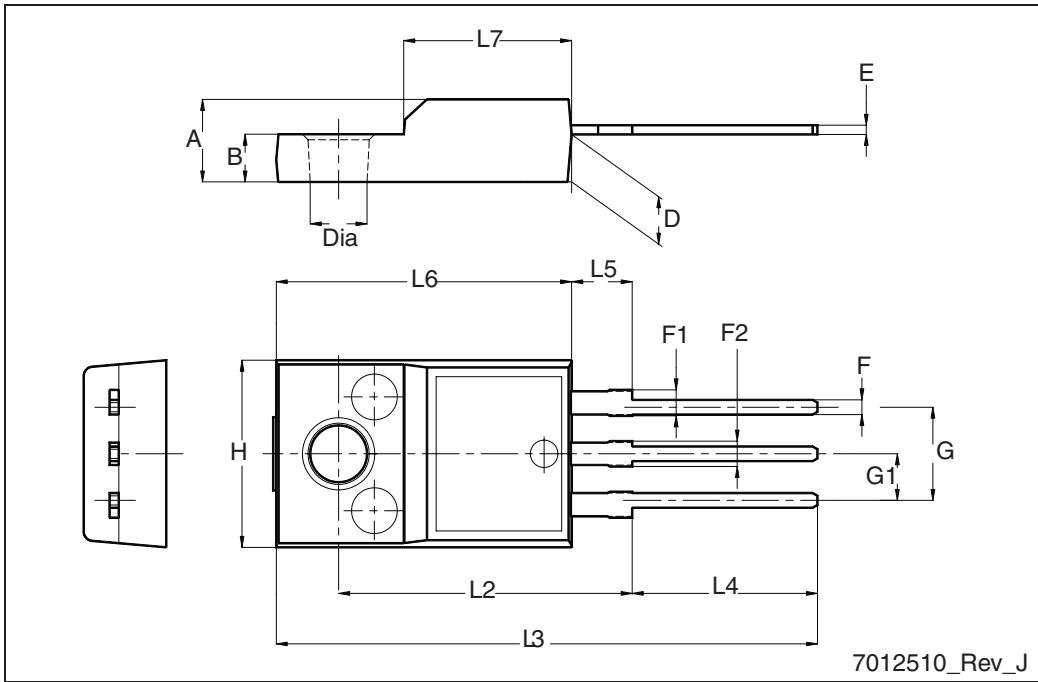
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



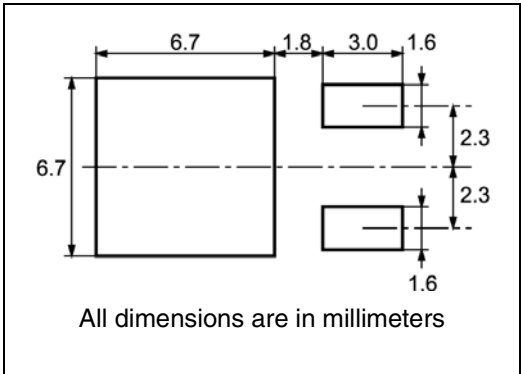
TO-220FP mechanical data

Dim.	mm		
	Mn.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

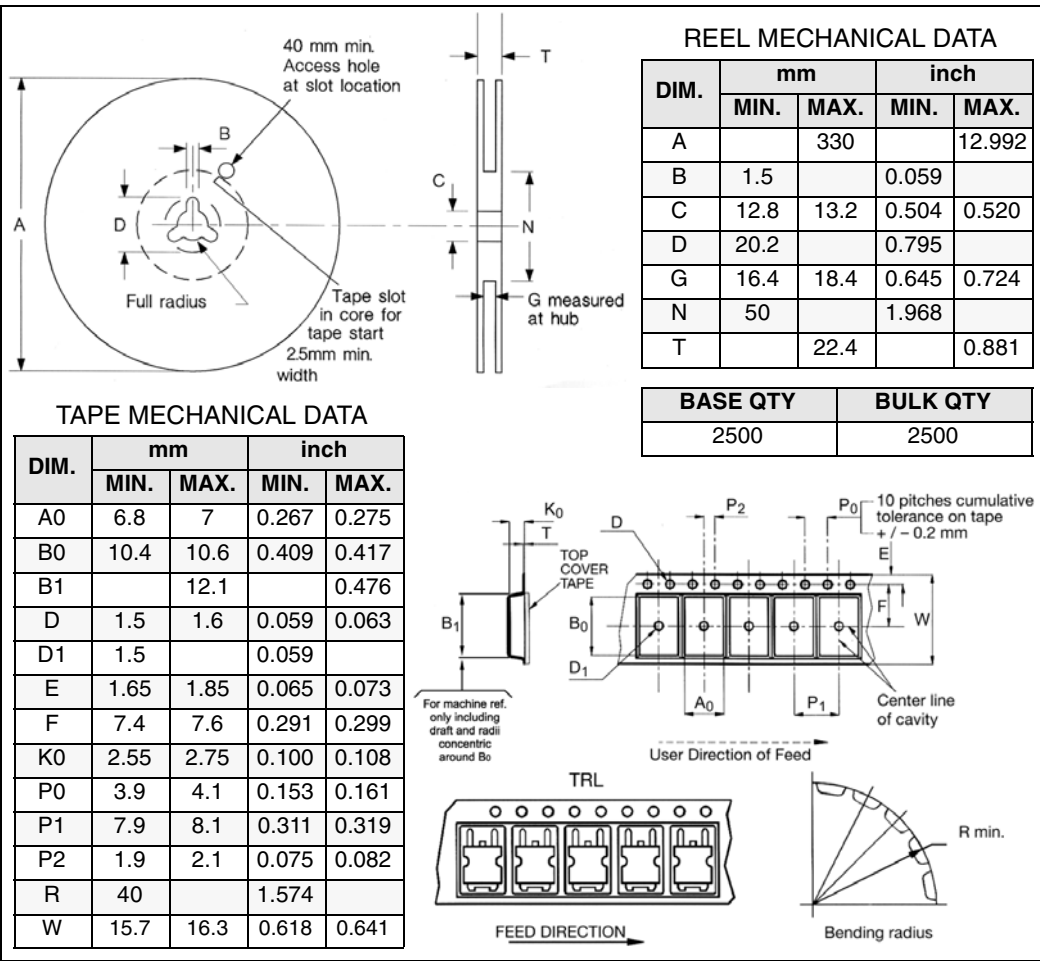


5 Packaging mechanical data

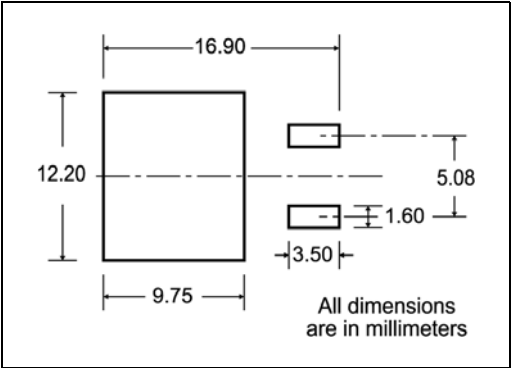
DPAK FOOTPRINT



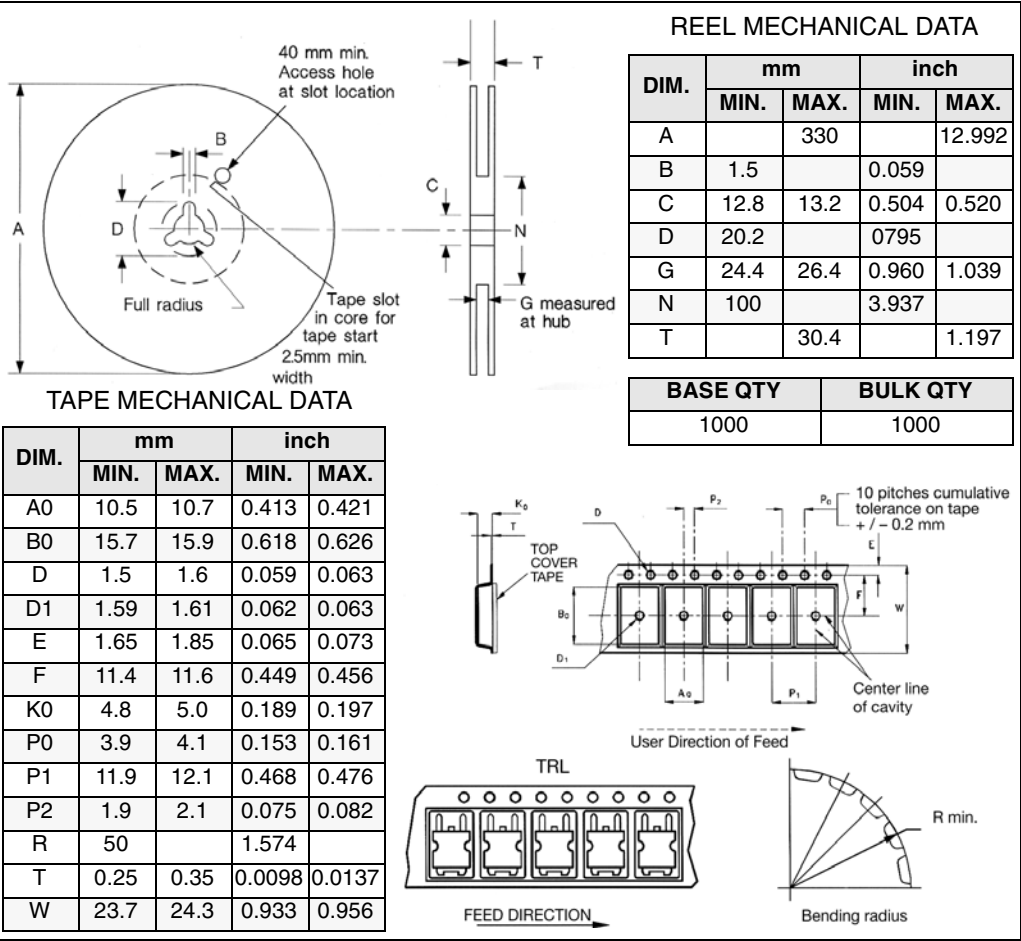
TAPE AND REEL SHIPMENT



D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
09-Feb-2007	1	First release
22-Feb-2007	2	Description has been updated
07-Mar-2007	3	The Figure 2 , Figure 4 , Figure 9 have been changed
17-Apr-2009	4	Added device in I ² PAK Updated all mechanical data

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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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